



ELECTRONICS, INC.
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NTE5962 & NTE5963 NTE5966 & NTE5967 Silicon Power Rectifier Diode, 25 Amp

Features:

- 25 Amp @ $T_C = +100^\circ\text{C}$
- 300 Amp Surge Capability
- Rugged Construction
- Available in Standard (NTE5962, NTE5966) and Reverse (NTE5963, NTE5967) Polarity

Absolute Maximum Ratings:

Peak Repetitive Reverse Voltage, V_{RRM}

NTE5962, NTE5963*	400V
NTE5966, NTE5967*	800V

Working Peak Reverse Voltage, V_{RWM}

NTE5962, NTE5963*	400V
NTE5966, NTE5967*	800V

DC Blocking Voltage, V_B

NTE5962, NTE5963*	400V
NTE5966, NTE5967*	800V

RMS Reverse Voltage, $V_{R(RMS)}$

NTE5962, NTE5963*	280V
NTE5966, NTE5967*	560V

Average Rectified Forward Currnt (Single phase, resistive load, 60Hz, $T_C = +150^\circ\text{C}$), I_O 25A

Non-Repetitive Peak Surge Current (Surge applied at rated load conditions), I_{FSM} 300A

Operating Junction Temperature Range, T_J -65° to $+175^\circ\text{C}$

Storage Temperature Range, T_{stg} -65° to $+175^\circ\text{C}$

Maximum Thermal Resistance, Junction-to-Case, R_{thJC} 1.2°C/W

Note 1. Standard polarity is cathode to case, (*) indicated anode to case.

Electrical Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Instantaneous Forward Voltage	V_F	$I_F = 57\text{A}$, $T_J = +25^\circ\text{C}$	—	—	1.7	V
Reverse Current	I_R	$V_{RRM} = \text{Rated Voltage}$, $T_C = +25^\circ\text{C}$	—	—	1.0	mA



